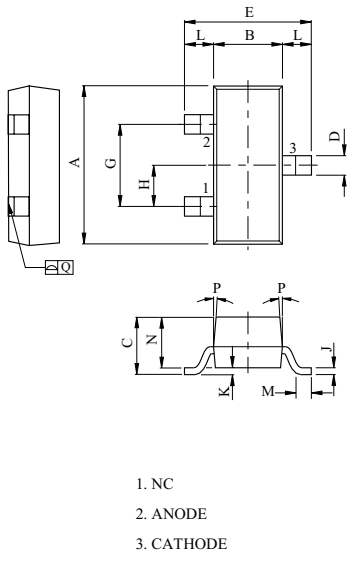
KDV386S

VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

VCO FOR UHF/VHF BAND.

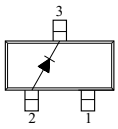
FEATURES

- High Capacitance Ratio : C_{1V}/C_{4V} =1.8 (Min.)
- Low Series Resistance. : r_S=0.9Ω (Max.)
- Good C-V Linearity.



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7°
Q	0.1 MAX

1. NC
2. ANODE
3. CATHODE

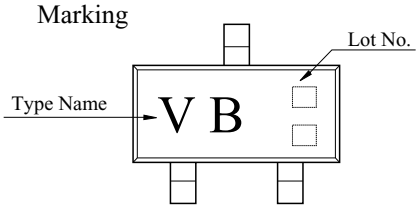


SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	15	V
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

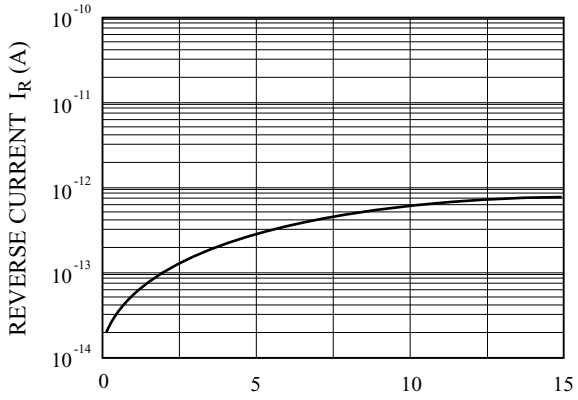
Marking



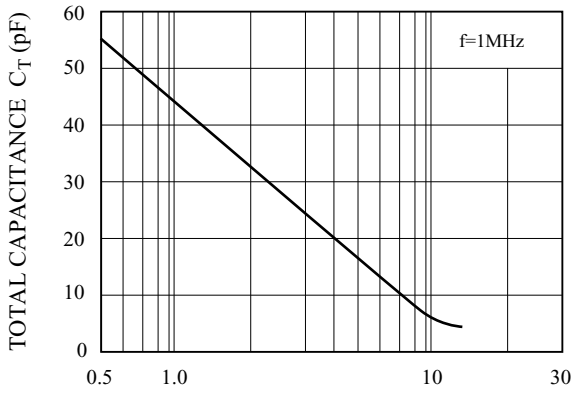
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	I_{R1}	V_R=15V	-	-	10	nA
	I_{R2}	V_R=15V, Ta=60℃	-	-	100	
Capacitance	C_{1V}	V_R=1V, f=1MHz	43.0	-	49.0	pF
	C_{4V}	V_R=4V, f=1MHz	18.5	-	25.5	
Capacitance Ratio	C_{1V}/C_{4V}	-	1.8	-	-	-
Series Resistance	r_S	V_R=5V, f=470MHz	-	-	0.9	Ω

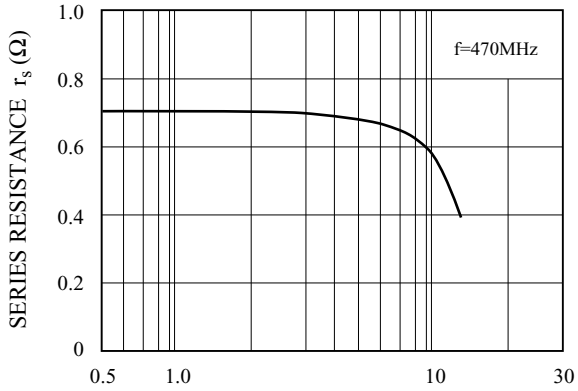
I_R - V_R



C_T - V_R



r_s - V_R



$\Delta(\text{LOG } C_T) / \Delta(\text{LOG } V_R)$ - V_R